

## BD175/177/179

# Medium Power Linear and Switching Applications

• Complement to BD 176/178/180 respectively



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Paramet	Value	Units	
V <sub>CBO</sub>	*Collector-Base Voltage	: BD175	45	V
		: BD177	60	V
		: BD179	80	V
$V_{CEO}$	Collector-Emitter Voltage	: BD175	45	V
		: BD177	60	V
		: BD179	80	V
V <sub>EBO</sub>	Emitter-Base Voltage		5	V
I <sub>C</sub>	Collector Current (DC)		3	А
I <sub>CP</sub>	*Collector Current (Pulse)		7	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)		30	W
T <sub>J</sub>	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter		Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining V	/oltage					
		: BD175	$I_C = 100 \text{mA}, I_B = 0$	45			V
		: BD177		60			V
		: BD179		80			V
I <sub>CBO</sub>	Collector Cut-off Current	: BD175	$V_{CB} = 45V, I_{E} = 0$			100	μΑ
		: BD177	$V_{CB} = 60V, I_{E} = 0$			100	μΑ
		: BD179	$V_{CB} = 80V, I_{E} = 0$			100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current		$V_{EB} = 5V, I_{C} = 0$			1	mA
h <sub>FE1</sub>	* DC Current Gain		$V_{CE} = 2V, I_{C} = 150 \text{mA}$	40		250	
h <sub>FE2</sub>			$V_{CE} = 2V, I_{C} = 1A$	15			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation V	oltage/	$I_C = 1A, I_B = 0.1A$			0.8	V
V <sub>BE</sub> (on)	* Base-Emitter On Voltage		$V_{CE} = 2V, I_C = 1A$			1.3	V
f <sub>T</sub>	Current Gain Bandwidth Produ	ıct	$V_{CE} = 10V, I_{C} = 250mA$	3			MHz

<sup>\*</sup> Pulse Test: PW=300μs, duty Cycle=1.5% Pulsed

## **h**<sub>FE</sub> Classificntion

Classification	6	10	16	
h <sub>FE1</sub>	40 ~ 100	63 ~ 160	100 ~ 250	
* Classification 16: Only BD175				

## **Typical Characteristics**

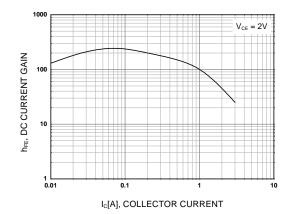


Figure 1. DC current Gain

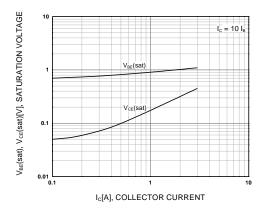


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

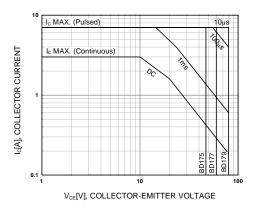


Figure 3. Safe Operating Area

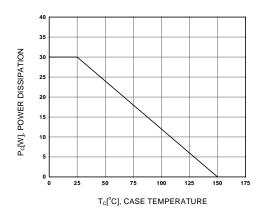
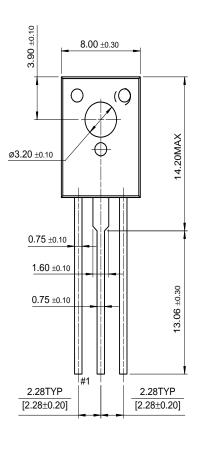


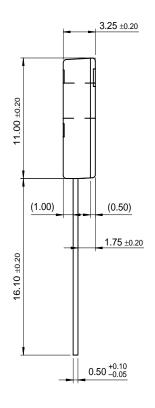
Figure 4. Power Derating

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## TO-126



**Package Demensions** 



Dimensions in Millimeters

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